

Vishay Semiconductors

Phase Control Thyristors (Hockey PUK Version), 910 A



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B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS					
I _{T(AV)}	910 A				
V _{DRM} /V _{RRM}	1200 V, 1600 V, 1800 V, 2000 V				
V_{TM}	1.80 V				
I _{GT}	100 mA				
TJ	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		910	Α			
I _{T(AV)}	T _{hs}	55	°C			
I _{T(RMS)}		1857	Α			
	T _{hs}	25	°C			
	50 Hz	15 700	۸			
I _{TSM}	60 Hz	16 400	Α			
10.	50 Hz	1232	kA ² s			
I ² t	60 Hz	1125	KA-S			
V _{DRM} /V _{RRM}		1200 to 2000	V			
tq	Typical	150	μs			
T _J		-40 to 125	°C			

VOLTAGE I	VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE VDRM/VRRM, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V		V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA						
	12	1200	1300							
VS-ST700CL	16	1600	1700	80						
V3-31700CL	18	1800	1900	00						
	20	2000	2100							



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ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	1857	
		t = 10 ms	No voltage		15 700	
Maximum peak, one-cycle	ı	t = 8.3 ms	reapplied		16 400	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		13 200	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	13 800	
Maximum I ² t for fusing		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	1232	
	l ² t	t = 8.3 ms			1125	
		t = 10 ms	100 % V _{RRM}		871	
		t = 8.3 ms	reapplied		795	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	ms, no voltage	e reapplied	12 321	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	1.00	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			\ \ \
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.40	mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.35	11122
Maximum on-state voltage	V_{TM}	$I_{pk} = 2000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.80	V
Maximum holding current	I _H	T 25 °C	T 05 00 and a col 40 V cold a load			mA
Typical latching current	IL	T _J = 25 °C, anode supply 12 V resistive load			1000	IIIA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1$ A/ μ s $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0	110
Typical turn-off time	t _q	$ \begin{array}{c} I_{TM} = 750 \text{ A, } T_J = T_J \text{ maximum, dl/dt} = 60 \text{ A/}\mu\text{s,} \\ V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate 0 V 100 } \Omega, t_p = 500 \mu\text{s} \\ \end{array} $	150	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	80	mA



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TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PANAIVIETEN	STIVIBOL	I Ex	ST CONDITIONS	Тур.	Max.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	Α
Maximum peak positive gate voltage	+V _{GM}	T. – T. maximum	t < 5 mg	20		V
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0] '
	I _{GT}	T _J = -40 °C	Maximum required gate	200	-	
DC gate current required to trigger		T _J = 25 °C		100	200	mA
		T _J = 125 °C	trigger/	50	-	
		T _J = -40 °C	current/voltage are the lowest value which will trigger all units	2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	V
	T _J = 125 °C			1.1	-	1
DC gate current not to trigger	I _{GD}	T _J = T _J maximum T _J = T _J maximum T _J = T _J maximum Value which will not trigger any unit with rated V _{DRM} anode to cathode applied		1	0	mA
DC gate voltage not to trigger	V _{GD}			0.	25	٧

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range	T _{Stg}		-40 to 150		
Maximum thermal resistance in action to be attain.	R _{thJ-hs}	DC operation single side cooled	0.073		
Maximum thermal resistance, junction to heatsink		DC operation double side cooled	0.031	K/W	
Maximum thermal registeres agas to be steinly	R _{thC-hs}	DC operation single side cooled	0.011	7 × W	
Maximum thermal resistance, case to heatsink		DC operation double side cooled	0.006		
Mounting force, ± 10 %			14 700 (1500)	N (kg)	
Approximate weight			255	g	
Case style		See dimensions - link at the end of datasheet	et B-PUK (TO-200		

△R _{thJ-hs} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL	SINUSOIDAL CONDUCTION		CONDUCTION	TEST COMPLETIONS	LINITO	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.009	0.009	0.006	0.006	$T_J = T_J$ maximum		
120°	0.011	0.011	0.011	0.011			
90°	0.014	0.014	0.015	0.015		K/W	
60°	0.020	0.020	0.021	0.021			
30°	0.036	0.036	0.036	0.036			

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC



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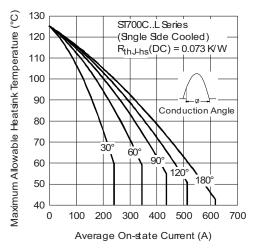


Fig. 1 - Current Ratings Characteristics

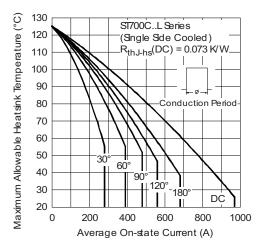


Fig. 2 - Current Ratings Characteristics

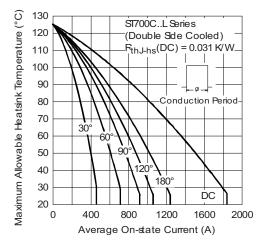


Fig. 3 - Current Ratings Characteristics

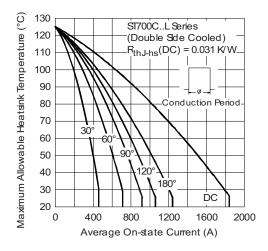


Fig. 4 - Current Ratings Characteristics

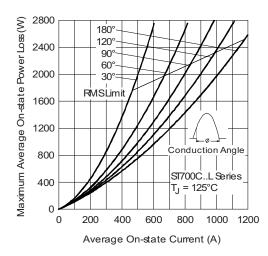


Fig. 5 - On-State Power Loss Characteristics

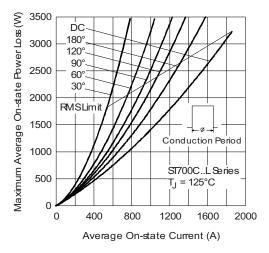
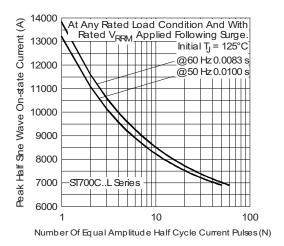


Fig. 6 - On-State Power Loss Characteristics

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Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

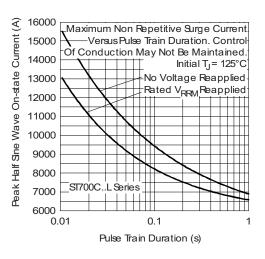


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

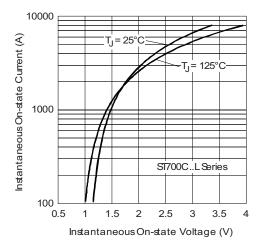


Fig. 9 - On-State Voltage Drop Characteristics

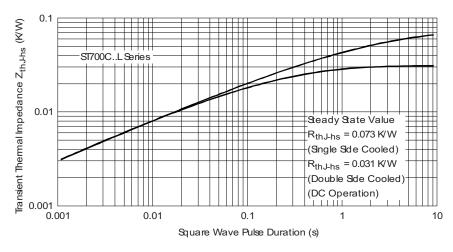


Fig. 10 - Thermal Impedance $Z_{thJ\text{-}hs}$ Characteristics

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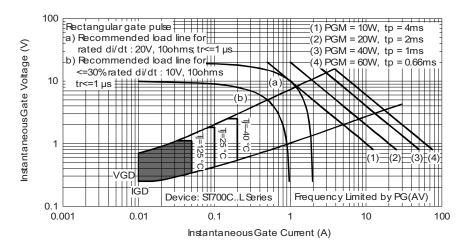
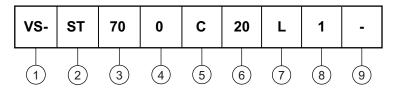


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



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2 - Thyristor

Essential part number

- 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

7 - L = PUK case B-PUK (TO-200AC)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95076			

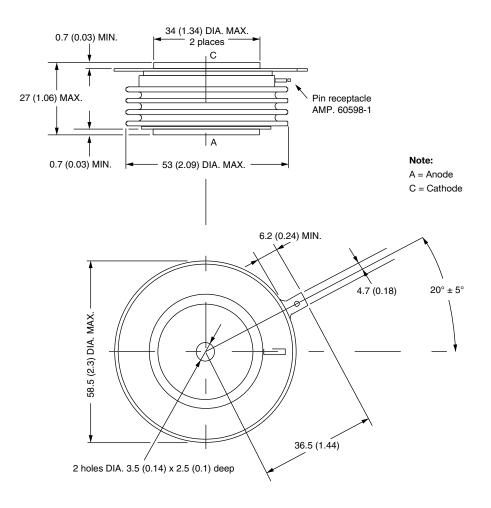


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B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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